25th RD50 Workshop (CERN)

Thursday, 20 November 2014

TCT techniques and HVCMOS - 500/1-001 - Main Auditorium (09:00 - 12:10)

-Conveners: Michael Moll

time	[id] title	presenter
09:00	[34] An Introduction to Edge-TCT measurements on irradiated HV-CMOSv3 sensors	WEISSER, Constantin
09:20	[14] Edge-TCT characterization of irradiated HV-CMOSv3 sensors	FERNANDEZ GARCIA, Marcos
09:40	[15] Edge-TCT studies of irradiated HVCMOS sensor (an update)	KRAMBERGER, Gregor
10:00	[4] E-TCT with laser beam directed parallel to strips	MANDIĆ, Igor
10:20	[33] Two Photon Absorption and carrier generation in semiconductors	Dr PALOMO PINTO, Fco. Rogelio
10:40	Coffee	
11:10	[35] TPA-TCT: A novel Transient Current Technique based on the Two Photon Absorption (TPA) process	Dr VILA ALVAREZ, Ivan
11:30	[25] TRACS: Transient Current Simulator	DE CASTRO MANZANO, Pablo
11:50	[46] Discussion on HVCMOS and TCT techniques	MOLL, Michael